NSN 5962-01-391-2513

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| View Online at https://aerobasegroup.com/nsn/5962-01-391-2513 |
|--|
| Maximum Power Dissipation Rating: |
| 550.0 milliwatts |
| Operating Tempurature Range: |
| -55.0/+125.0 degrees celsius |
| End Application: |
| Cv-3993/sys-2 e/i fscm 21877 |
| Features Provided: |
| Programmed and electrostatic sensitive |
| Inclosure Configuration: |
| Dual-in-line |
| Output Logic Form: |
| Complementary-metal oxide-semiconductor logic |
| Case Outline Source And Designator: |
| D-9 mil-m-38510 |
| Product Name: |
| 2k x 8 bit, prom |
| Voltage Rating And Type Per Characteristic: |
| 4.5 volts applied and 5.5 volts applied |
| Time Rating Per Chacteristic: |
| 35.00 nanoseconds af output megawatts |
| Memory Device Type: |
| Prom |
| Hybrid Technology Type: |
| Monolithic |
| Special Features: |
| One time programmable |
| Test Data Document: |
| 81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification |
| format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain |
| environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-883 |
| standard (includes industry or association standards, individual manufactureer standards, etc.). |
| Terminal Type And Quantity: |
| 24 printed circuit |
| Specification Data: |
| 67268-5962-88734 government standard |
| Specification Or Standard: |
| 03 type and I case and a finish |
| Departure From Cited Designator: |
| Programmed per: 301018 (21877) |
| Shelf Life: |

Demilitarization:

Unit Of Measure:

N/a

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